

## **Notification about the transfer of the semiconductor business**

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

**Nuvoton Technology Corporation Japan**

**MTM861280LBF**  
 Silicon P-channel MOSFET

For Switching

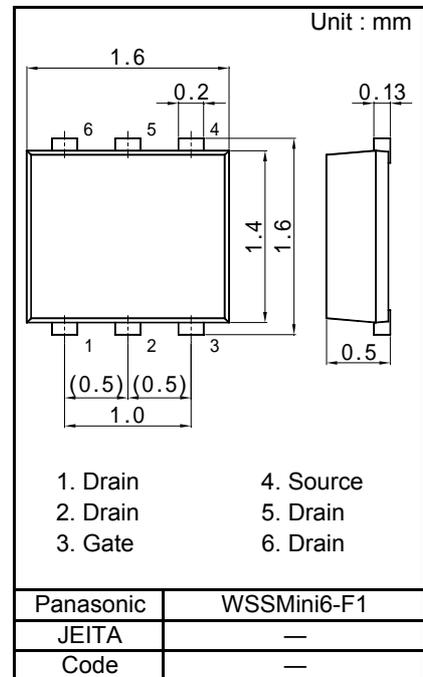
■ Features

- Low drain-source On-state Resistance  
 : RDS(on) typ. = 300 mΩ (VGS = -4.0 V)
- Halogen-free / RoHS compliant  
 (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : ML

■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)



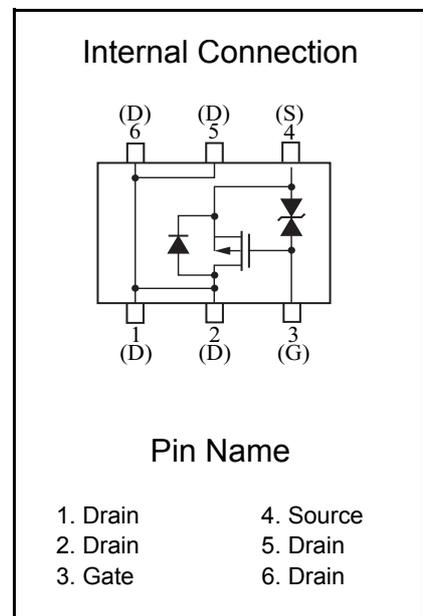
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	VDS	-20	V
Gate to Source Voltage	VGS	±12	
Drain Current	ID	-1.0	
Drain Current (Pulsed) *1	IDp	-4.0	A
Total Power Dissipation	PD1 *2	540	mW
	PD2 *3	150	
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to +85	
Storage Temperature Range	Tstg	-55 to +150	

Note) \*1 t ≤ 10 μs, Duty cycle ≤ 1 %

\*2 Glass epoxy substrate (25.4 × 25.4 × t 0.8 mm) coated with copper foil (more than 300 mm<sup>2</sup>)

\*3 Non-heat sink



■ Electrical Characteristics Ta = 25 °C ± 3 °C

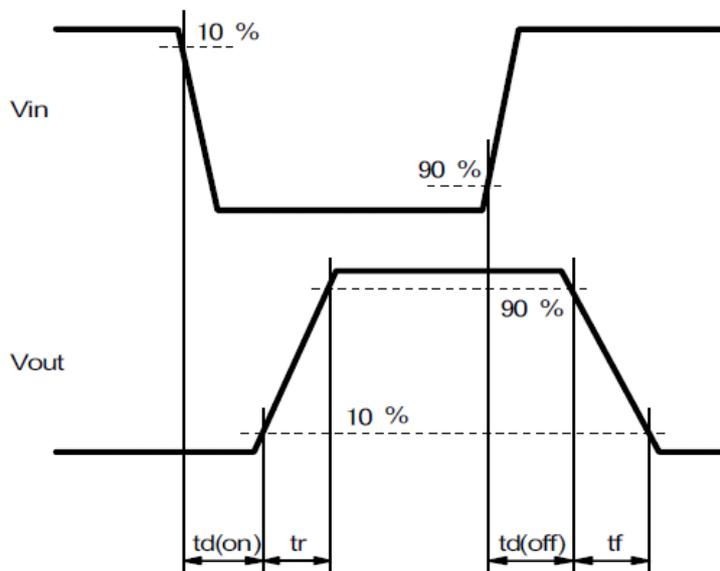
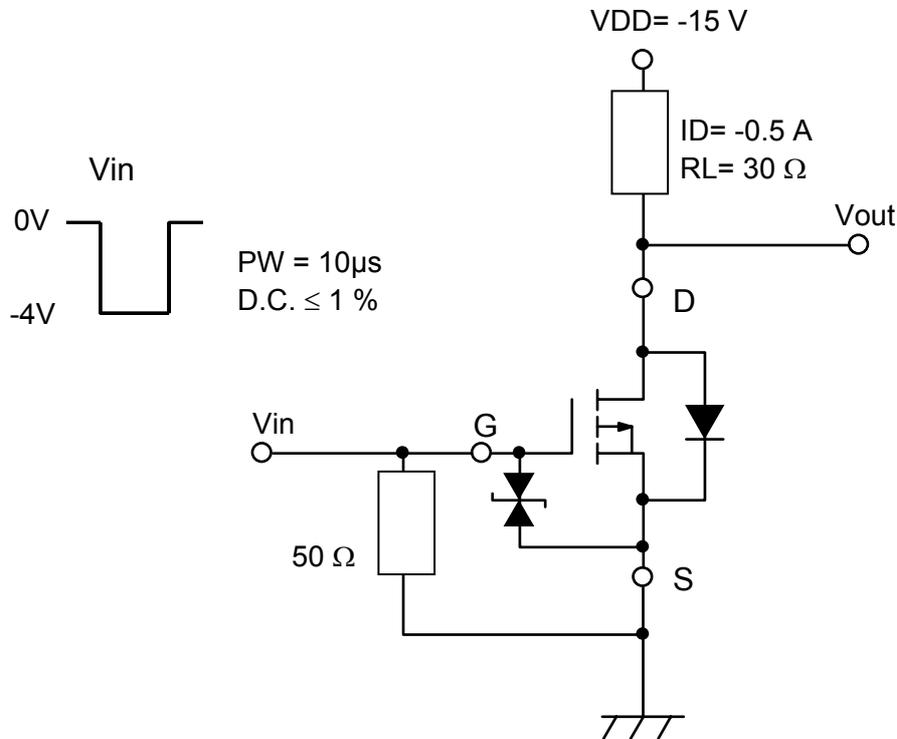
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1.0 mA, VGS = 0 V	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0 V			-1.0	μA
Gate-source Leakage Current	IGSS	VGS = ±10 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10 V	-0.45	-1.0	-1.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = -0.5 A, VGS = -4.0 V		300	420	mΩ
	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		420	560	
Forward transfer admittance *1	Yfs	ID = -0.5 A, VDS = -10 V	1.0	2.0		S
Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V f = 1 MHz		80		pF
Output Capacitance	Coss			12		
Reverse Transfer Capacitance	Crss			12		
Turn-on Delay Time *2	td(on)	VDD = -15 V, VGS = 0 to -4 V		12		ns
Rise Time *2	tr	ID = -0.5 A		6		
Turn-off Delay Time *2	td(off)	VDD = -15 V, VGS = -4 to 0 V		17		ns
Fall Time *2	tf	ID = -0.5 A		10		

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

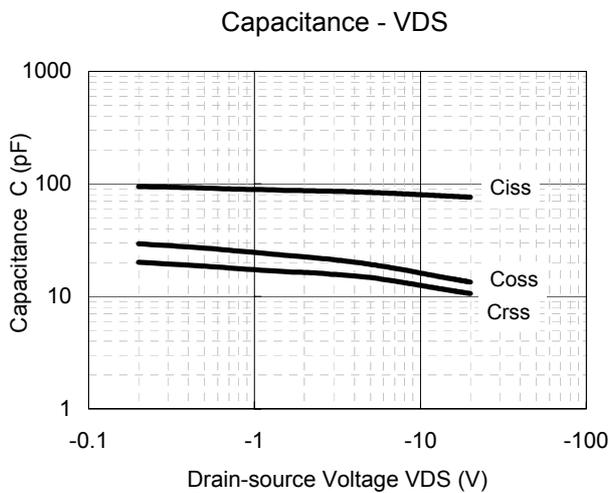
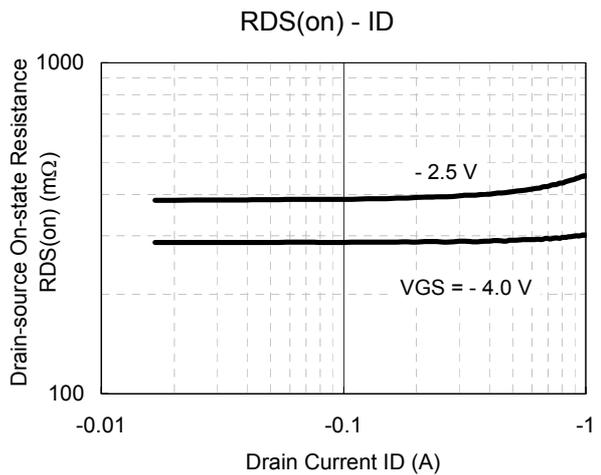
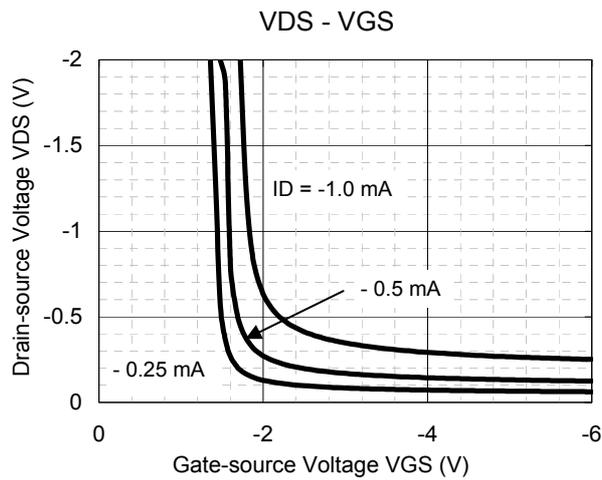
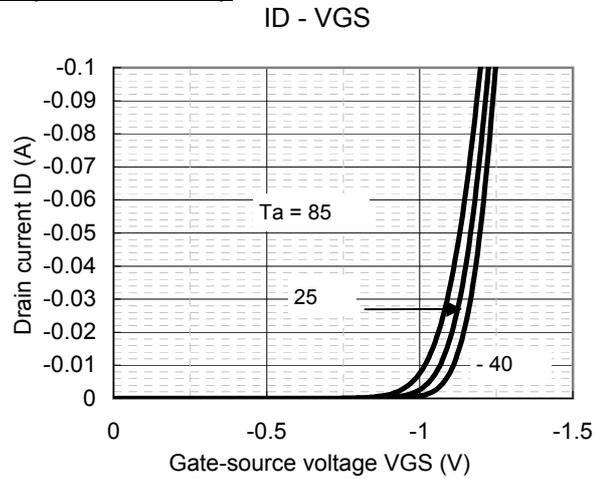
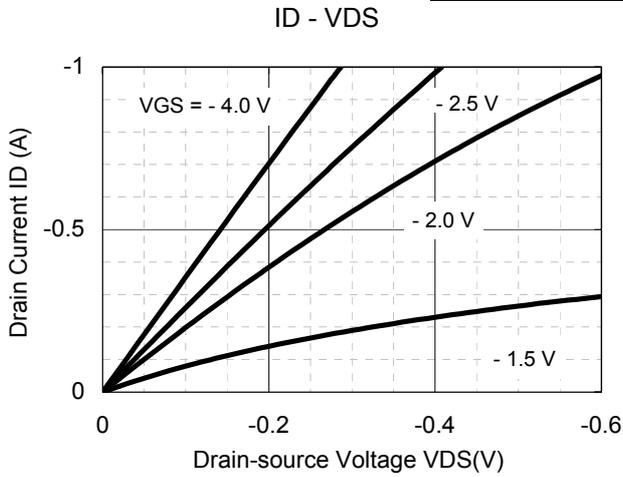
\*1 Pulse test

\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

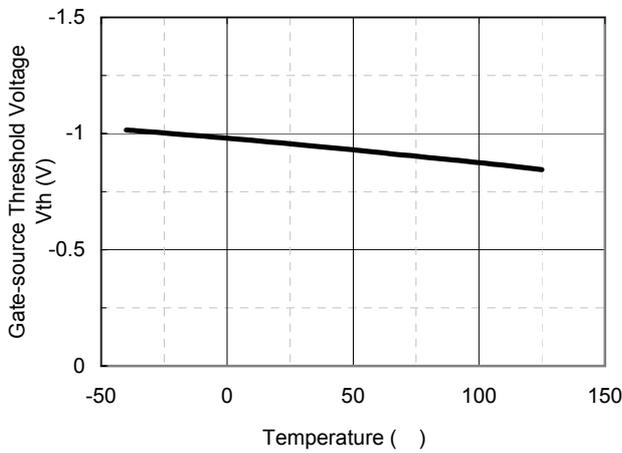


Technical Data ( reference )

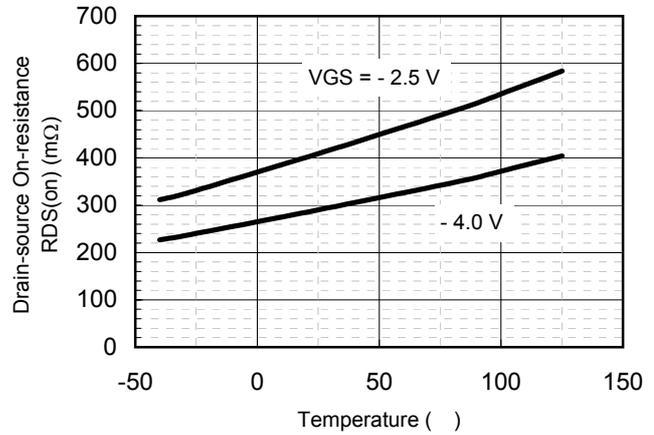


Technical Data ( reference )

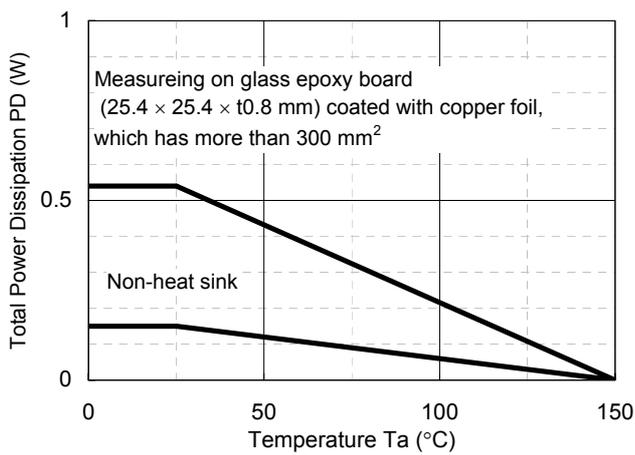
Vth - Ta



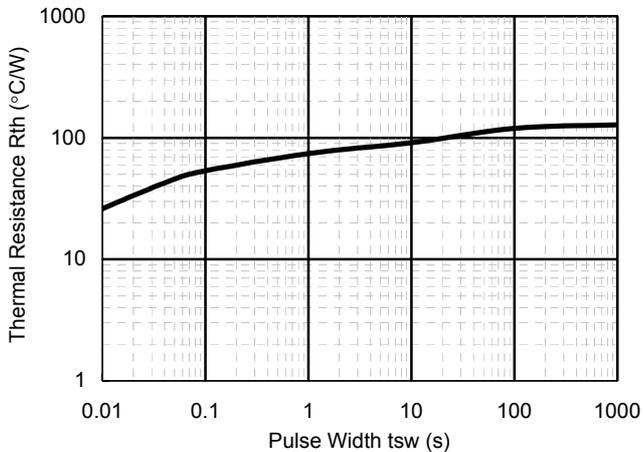
RDS(on) - Ta



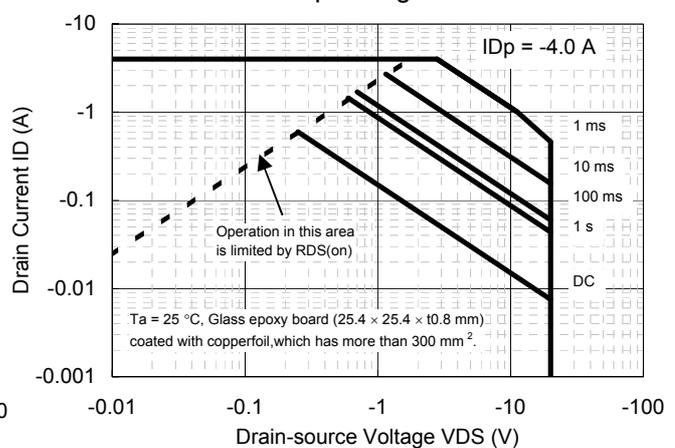
PD - Ta



Rth - tsw

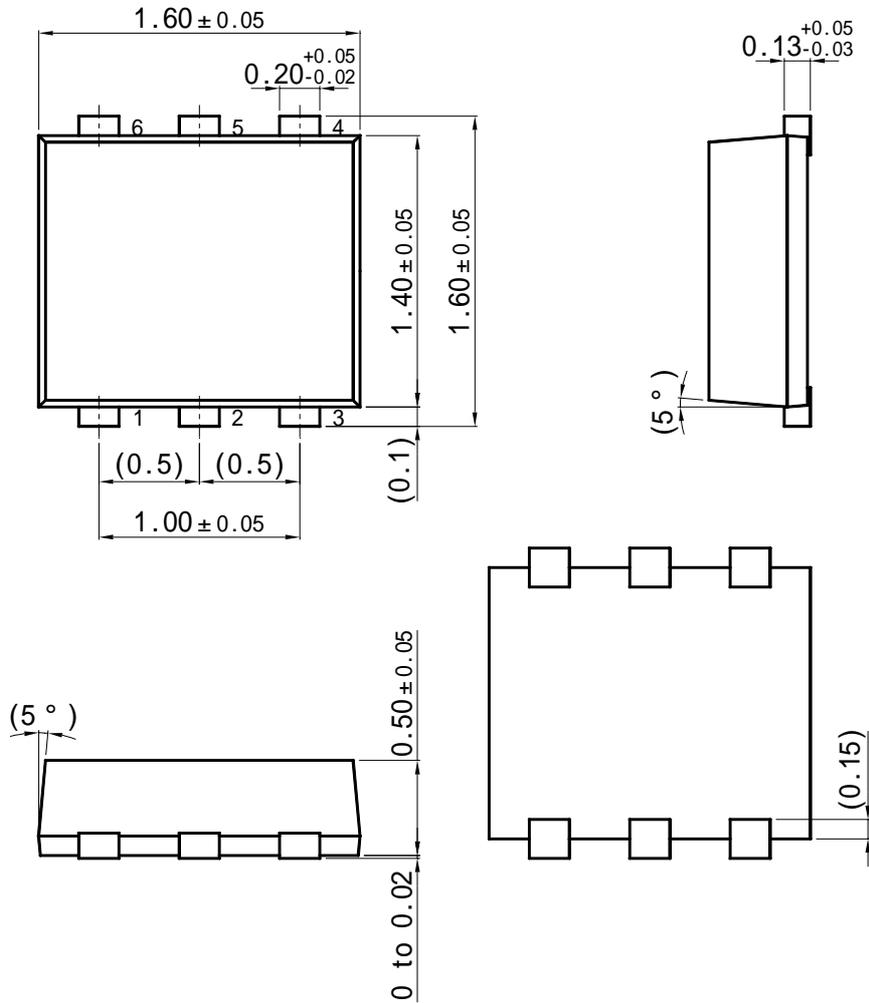


Safe Operating Area

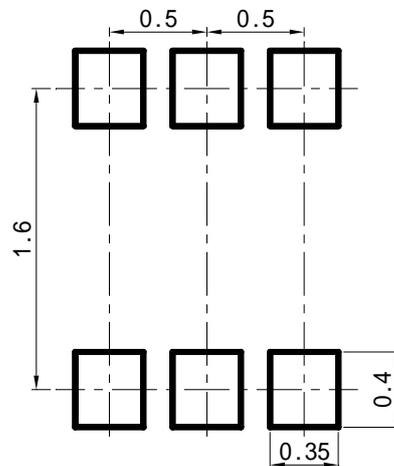


WSSMini6-F1

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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